# **BGA7124**

### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

Rev. 00.07 — 16 July 2009

Objective data sheet

### 1. Product profile

#### 1.1 General description

The BGA7124 MMIC is a one-stage driver amplifier, offered in a low-cost leadless surface-mount package. It delivers 25 dBm output power at 1 dB gain compression and a superior performance for various narrowband-tuned application circuits for frequencies up to 2700 MHz.

#### 1.2 Features

- 400 MHz to 2700 MHz frequency operating range
- 16 dB small signal gain at 2 GHz
- 25 dBm output power at 1 dB gain compression
- Integrated active biasing
- External matching allows broad application optimization of the electrical performance
- 3.3 V / 5 V single supply operation
- Power savings features:
  - ◆ Simple quiescent current adjustment allows class-AB operation
  - lacktriangle Logic-level shutdown control pin reduces supply current to 4  $\mu A$
- ESD protection at all pins

#### 1.3 Applications

- Wireless infrastructure (base station, repeater)
- E-metering
- Broadband CPE
- Satellite Master Antenna TV (SMATV)
- Industrial applications
- W-LAN / ISM / RFID

#### 1.4 Quick reference data

#### Table 1. Quick reference data

 $Z_S = Z_L = 50 \ \Omega$ ,  $\overline{SHDN} = V_{I(D)H(SHDN)}$  (shutdown disabled). Typical values at  $V_{CC} = 5 \ V$ ;  $T_{case} = 25 \ ^{\circ}C$ , ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_{Cq}$	adjustable quiescent collector current		5	-	170	mA
f	frequency		[ <u>1</u> ] 400	-	2700	MHz



#### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

Table 1. Quick reference data ...continued

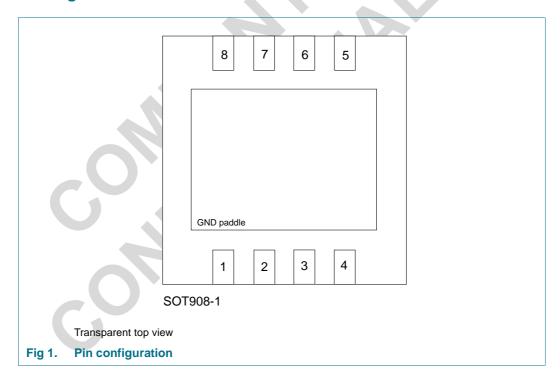
 $Z_S = Z_L = 50 \ \Omega$ ,  $\overline{SHDN} = V_{I(D)H(SHDN)}$  (shutdown disabled). Typical values at  $V_{CC} = 5 \ V$ ;  $T_{case} = 25 \ ^{\circ}C$ , ; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	gain power	f = 2140 MHz	<u>[3]</u> _	15	-	dB 🕏
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 2140 MHz	[3] _	25	-	dBm
IP3 <sub>O</sub>	output third-order intercept point	f = 2140 MHz	[2][3]	38	-	dBm

<sup>[1]</sup> Operation outside this range is possible but parameters are not guaranteed.

### 2. Pinning information

#### 2.1 Pinning



BGA7124\_1 © NXP B.V. 2009. All rights reserved.

<sup>[2]</sup>  $P_{O(tone)} = 8 \text{ dBm}$ ; tone spacing = 10 MHz,  $f_1 = 850 \text{ MHz}$  to 1000 MHz;  $f_2 = 1800 \text{ MHz}$  to 2400 MHz; higher IMD3 product.

<sup>[3]</sup> Applicable to class-A operation;  $I_{Cq} = \langle tbd \rangle$  mA.

### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

#### 2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description	
n.c.	1, 4	not connected	2
RF_OUT/V <sub>CC</sub>	2, 3	RF output for the power amplifier and DC supply input for the RF transistor collector[1]	
V <sub>CC(bias)</sub>	5	bias supply voltage[2]	
SHDN	6	shutdown control function enabled / disabled	
RF_IN	7	RF input for the power amplifier[1]	
ICQ_ADJ	8	I <sub>Cq</sub> quiescent collector current adjustment by an external resistor	
GND	GND paddle	RF ground and DC ground[3]	

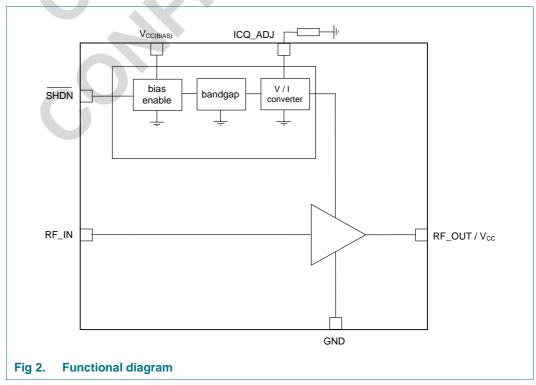
- [1] This pin is DC-coupled and requires an external DC-blocking capacitor.
- [2] RF decoupled.
- [3] The center metal base of the SOT908-1 also functions as heatsink for the power amplifier.

### 3. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BGA7124	HVSON8	plastic thermal enhanced very thin small outline package; no leads; 8 terminals; body $3 \times 3 \times 0.85$ mm	SOT908-1				

## 4. Functional diagram



@ NXP B.V. 2009. All rights reserved.

#### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

#### 5. Shutdown control

Table 4. Shutdown control

				1//
Mode	Mode description	Function description	SHDN	Unit
Idle	medium power MMIC fully off; minimal supply current	shutdown control enabled	0	digital logic
TX	medium power MMIC transmit mode	shutdown control enabled	1	digital logic

### 6. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-	5.2	V
I <sub>CC</sub>	supply current	V <sub>CC</sub> = 5.2 V	-	<tbd></tbd>	mΑ
P <sub>i(RF)</sub>	RF input power		-	<tbd></tbd>	dBm
P <sub>tot</sub>	total power dissipation		-	<tbd></tbd>	W
T <sub>case</sub>	case temperature		-40	+85	°C
Tj	junction temperature		-	150	°C

### 7. Thermal characteristics

#### Table 6. Thermal characteristics

	Parameter	Conditions	Тур	Max	Unit
R <sub>th(j-case)</sub>	thermal resistance from junction to case	$T_{case}$ = 85 °C; $V_{CC}$ = 5 V; $I_{CC}$ = 85 mA	25	30	K/W

### 8. Static characteristics

#### Table 7. Characteristics

 $Z_S = Z_L = 50 \ \Omega$ ,  $\overline{SHDN} = V_{I(D)H(SHDN)}$  (shutdown disabled). Typical values at  $V_{CC} = 3.3 \ V / 5 \ V$ ;  $T_{case} = 25 \ ^{\circ}C$ , ; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{CC}$	supply voltage	range for $V_{CC} =  V (typ)$		3.0	3.3	3.6	V
		range for $V_{CC} =  V (typ)$		4.8	5.0	5.2	V
I <sub>Cq</sub>	adjustable quiescent collector current			5	-	170	mΑ
I <sub>CC</sub>	supply current	V <sub>CC</sub> = 5.2 V		-	-	<tbd></tbd>	mΑ
I <sub>CC(SHDN)</sub>	shutdown supply current	$\overline{SHDN} = V_{I(D)L(SHDN)};$	[1]	2	4	<tbd></tbd>	μΑ
$V_{I(D)L(SHDN)}$	shutdown logic LOW digital input voltage			0	-	1.5	V
V <sub>I(D)H(SHDN)</sub>	shutdown logic HIGH digital input voltage			2.5	-	$V_{CC}$	V
I <sub>I(D)L(SHDN)</sub>	shutdown logic LOW digital input current	$\overline{SHDN} = V_{I(D)L(SHDN)}$	[1]	-	-	1	μΑ
I <sub>I(D)H(SHDN)</sub>	shutdown logic HIGH digital input current	$\overline{SHDN} = V_{I(D)H(SHDN)}$	[1]	-	-	1	μΑ

<sup>[1]</sup> Defined across  $V_{CC}$  = 3.0 V to 3.6 V and 4.8 V to 5.2 V;  $T_{case}$  = -40 °C to +85 °C.

@ NXP B.V. 2009. All rights reserved.

**NXP Semiconductors** 

#### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

9. Dynamic characteristics

Table 8. Characteristics at  $V_{CC} = 5 \text{ V}$   $Z_S = Z_L = 50 \Omega$ ,  $\overline{SHDN} = V_{I(D)H(SHDN)}$  (shutdown disabled). Typical values at  $V_{CC} = 5 \text{ V}$ ;  $T_{case} = 25 \text{ °C}$ , NXP application circuit; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	frequency		<u>[1]</u> 400	-	2700	MHz
Gp	gain power	f = 900 MHz	[2] _	23	-	dB
		f = 1900 MHz	[2] -	16	-	dB
		f = 2140 MHz	[2] -	15	-	dB
		f = 2450 MHz	[2] _	<tbd></tbd>	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 900 MHz	[2] _	25	-	dBm
		f = 1900 MHz	[2] _	25	-	dBm
		f = 2140 MHz	[2] -	25	-	dBm
		f = 2450 MHz	[2] -	<tbd></tbd>	-	dB
IP3 <sub>O</sub>	output third-order intercept point	f = 900 MHz	[2][3]	38	-	dBm
		f = 1900 MHz	[2][3]	38	-	dBm
		f = 2140 MHz	[2][3]	38	-	dBm
		f = 2450 MHz	[2][3]	<tbd></tbd>	-	dB
NF	noise figure	f = 900 MHz	[2][4]	4.5	-	dB
		f = 1900 MHz	[2][4]	5.5	-	dB
		f = 2140 MHz	[2][4]	6.5	-	dB
		f = 2450 MHz	[2][4]	<tbd></tbd>	-	dB
RL <sub>in</sub>	input return loss	f = 900 MHz	[2]	-12.0	-	dB
		f = 1900 MHz	[2] _	-10.0	-	dB
		f = 2140 MHz	[2] _	-11.0	-	dB
		f = 2450 MHz	[2] _	<tbd></tbd>	-	dB
RL <sub>out</sub>	output return loss	f = 900 MHz	[2] _	-8.0	-	dB
		f = 1900 MHz	[2] _	-14.0	-	dB
		f = 2140 MHz	[2] _	-13.0	-	dB
		f = 2450 MHz	[2] _	<tbd></tbd>	-	dB
Icc	supply current	$V_{CC} = 5 \text{ V}$	[2] _	175	-	mA

<sup>[1]</sup> Operation outside this range is possible but parameters are not guaranteed.

<sup>[2]</sup> Applicable to class-A operation;  $I_{Cq} = 175 \text{ mA}$ .

<sup>[3]</sup>  $P_{O(tone)} = 8 \text{ dBm}$ ; tone spacing = 10 MHz,  $f_1 = 840 \text{ MHz}$  to 960 MHz;  $f_2 = 1900 \text{ MHz}$  to 2200 MHz; higher IMD3 product.

Defined at  $P_{IN} = -40$  dBm; small signal conditions.

#### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

Table 9. Characteristics at  $V_{CC} = 3.3 \text{ V}$ 

 $Z_S = Z_L = 50 \ \Omega$ ,  $\overline{SHDN} = V_{I(D)H(SHDN)}$  (shutdown disabled). Typical values at  $V_{CC} = 3.3 \ V$ ;  $T_{case} = 25 \ ^{\circ}\text{C}$ , NXP application circuit; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	frequency	Conditions	[1] 400	- 46.	2700	MHz
G <sub>p</sub>	gain power	f = 900 MHz	[2][3]	- <tbd></tbd>	-	dB
G <sub>p</sub>	gain power	f = 1900 MHz	[2][3]	16		dB
			[2][3]			
		f = 2140 MHz	[2][3]	<tbd></tbd>	-	dB
		f = 2450 MHz		<tbd></tbd>	-	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression	f = 900 MHz	[2][3] _	<tbd></tbd>	-	dBm
		f = 1900 MHz	[2][3]	23	-	dBm
		f = 2140 MHz	[2][3]	<tbd></tbd>	-	dBm
		f = 2450 MHz	[2][3]	<tbd></tbd>	-	dB
IP3 <sub>O</sub>	output third-order intercept point	f = 900 MHz	[2][3][4]	<tbd></tbd>	-	dBm
		f = 1900 MHz	[2][3][4]	36	-	dBm
		f = 2140 MHz	[2][3][4]	<tbd></tbd>	-	dBm
		f = 2450 MHz	[2][3][4]	<tbd></tbd>	-	dB
NF	noise figure	f = 900 MHz	[2][3][5]	<tbd></tbd>	-	dB
		f = 1900 MHz	[2][3][5]	4.7	-	dB
		f = 2140 MHz	[2][3][5]	<tbd></tbd>	-	dB
		f = 2450 MHz	[2][3][5]	<tbd></tbd>	-	dB
RL <sub>in</sub>	input return loss	f = 900 MHz	[3] _	<tbd></tbd>	-	dB
	( ) Y	f = 1900 MHz	[3] _	<tbd></tbd>	-	dB
		f = 2140 MHz	[3] _	<tbd></tbd>	-	dB
		f = 2450 MHz	[3] _	<tbd></tbd>	-	dB
RL <sub>out</sub>	output return loss	f = 900 MHz	[3] _	<tbd></tbd>	-	dB
		f = 1900 MHz	[3] _	<tbd></tbd>	-	dB
		f = 2140 MHz	[3] _	<tbd></tbd>	-	dB
		f = 2450 MHz	[3] _	<tbd></tbd>	-	dB
lcc	supply current	$V_{CC} = 3.3 \text{ V}$	[2][3]	175	-	mA

<sup>[1]</sup> Operation outside this range is possible but parameters are not guaranteed.

### 10. Reliability information

#### Table 10. Reliability

Life test	Conditions	Intrinsic failure rate
HTOL	confidence level 60 %; $T_j$ = 55 °C; activation energy = 0.7 eV; acceleration factor determined by Arrhenius	XX

BGA7124\_1 © NXP B.V. 2009. All rights reserved

<sup>[2]</sup> Defined across  $V_{CC}$  = 3.0 V to 3.6 V;  $T_{case}$  = -40 °C to +85 °C.

<sup>[3]</sup> Applicable to class-A operation;  $I_{Cq} = 175 \text{ mA}$ .

<sup>[4]</sup>  $P_{o(tone)} = 8$  dBm; tone spacing = 10 MHz,  $f_1 = 850$  MHz to 1000 MHz;  $f_2 = 1800$  MHz to 2400 MHz; higher IMD3 product.

<sup>[5]</sup> Defined at  $P_{IN} = -40$  dBm; small signal conditions.

#### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

### 11. Package outline

HVSON8: plastic thermal enhanced very thin small outline package; no leads; 8 terminals; body  $3 \times 3 \times 0.85 \text{ mm}$ 

SOT908-1

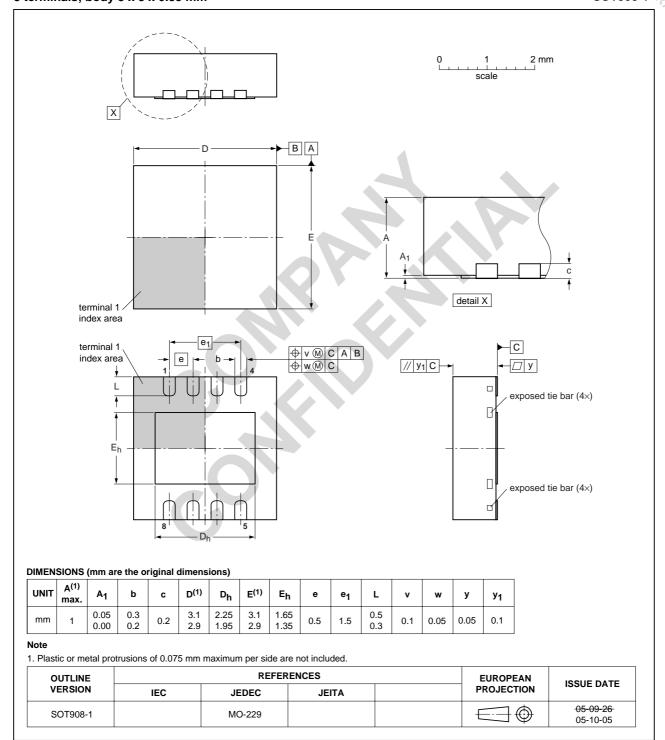


Fig 3. Package outline SOT908-1 (HVSON8)

@ NXP B.V. 2009. All rights reserved.

### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

### 12. Abbreviations

Table 11. Abbreviations

		, YA
Acronym	Description	122.0
CPE	Customer-Premises Equipment	7
ESD	ElectroStatic Discharge	
HTOL	High Temperature Operating Life	
ISM	Industrial, Scientific and Medical	
MMIC	Monolithic Microwave Integrated Circuit	
RFID	Radio Frequency IDentification	
TX	Transmit	
W-LAN	Wideband Code Division Multiple Access	

# 13. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGA7124_1	<tbd></tbd>	Objective data sheet	-	-

#### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

### 14. Legal information

#### 14.1 Data sheet status

NXP Semiconductors		BGA7124
		400 MHz to 2700 MHz 1/4 W high linearity Si amplifier
14. Legal information		DRA DRA DRA
I4.1 Data sheet	status	DRAKT DRAKT D
Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
	0 "" "	This is a second of the second
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions"
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### 14.2 **Definitions**

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

#### 14.3 **Disclaimers**

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage.

NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

#### 14.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

#### 15. Contact information

For more information, please visit: http://www.nxp.com

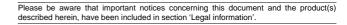
For sales office addresses, please send an email to: salesaddresses@nxp.com

**NXP Semiconductors** 

### 400 MHz to 2700 MHz 1/4 W high linearity Si amplifier

### 16. Contents

1	Product profile	. 1
1.1	General description	. 1
1.2	Features	. 1
1.3	Applications	
1.4	Quick reference data	. 1
2	Pinning information	. 2
2.1	Pinning	. 2
2.2	Pin description	. 3
3	Ordering information	. 3
4	Functional diagram	. 3
5	Shutdown control	. 4
6	Limiting values	. 4
7	Thermal characteristics	. 4
8	Static characteristics	. 4
9	Dynamic characteristics	. 5
10	Reliability information	. 6
11	Package outline	. 7
12	Abbreviations	. 8
13	Revision history	. 8
14	Legal information	. 9
14.1	Data sheet status	. 9
14.2	Definitions	. 9
14.3	Disclaimers	. 9
14.4	Trademarks	. 9
15	Contact information	. 9
16	Contents	10







Document identifier: BGA7124\_1



founded by